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教師研究成果資料明細

研究計畫

1.蔡宗叡 國科會 2011.12.1 ~2012.10.31

複晶矽薄膜矽與二氧化矽結構上之磷摻雜劑量損失行為模式

SCI、SSCI、A&HCI、EI、TSSCI期刊論文

1.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai), 2010-11, (已刊登)

ICSICT-2006: 2006 8th International Conference on Solid-State and Integrated Circuit Technology, Proceedings 1卷3期:1838頁~1840頁
A 5V/200V SOI Device with a Vertically Linear Graded Drift Region

2.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai), 2011-08, (已刊登)

ICEMI 1卷期:85頁~88頁
Application of Multi-Lateral Double Diffused Field Ring in Ultrahigh-Voltage Device MOS Transistor Design

3.蔡宗叡(Jung-Ruey Tsai)、許健(Gene Sheu)、楊紹明(Shao-Ming Yang), 2011-08, (已刊登)

ICEMI 1卷期:235頁~238頁
Analysis of Si₃N₄ passivation effect by self-consistent electro-thermal-mechanical simulation in AlGaN/GaN heterostructure HEMTs

4.楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai), 2011-08, (已刊登)

ICEMI 1卷期:239頁~242頁
Effects of SiO₂ passivation on AlGaN/GaN HEMT by self-consistent electro-thermal-mechanical simulation

5.許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)*、楊紹明(Shao-Ming Yang), 2011-08, (已刊登)

The Ninth International Conference on Electronic Measurement & Instruments 4卷期:5頁~9頁

Improvement of Electrical Characteristics in LDMOS by the Insertion of PBL and Gate Extended Field Plate Technologies

6.許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)*、楊紹明(Shao-Ming Yang), 2011-08, (已刊登)

ICEMI 4卷期:5頁~9頁

Improvement of Electrical Characteristics in LDMOS by the Insertion of PBL

非SCI、SSCI、A&HCI、EI、TSSCI...等具審查機制論文

1. 楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)
, 2010-11, ()

ICSICT 2010 2010卷2010期:1838頁~1840頁

A 5V/200V SOI Device with a Vertically Linear Graded Drift Region

2. 楊紹明(Shao-Ming Yang)、許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)
, 2010-11, (已刊登)

ICSICT 2010 卷期:1838頁~1840頁

A 5V/200V SOI Device with a Vertically Linear Graded Drift Region

3. 許健(Gene Sheu)、蔡宗叡(Jung-Ruey Tsai)、楊紹明(Shao-Ming Yang)
, 2011-11, (已刊登)

tencon 2010 卷期:1356頁~1360頁

Self-Consistent Electro-Thermo-Mechanical Analysis of AlN Passivation Effect on
AlGaN/GaN HEMTs

4. 蔡宗叡(Jung-Ruey Tsai)、許健(Gene Sheu)、楊紹明(Shao-Ming Yang)
, 2011-11, (已刊登)

tencon 2010 卷期:760頁~763頁

Development of ESD Robustness Enhancement of a Novel 800V LDMOS Multiple
RESURF with Linear P-top Rings

5. 許健(Gene Sheu)、楊紹明(Shao-Ming Yang)、蔡宗叡(Jung-Ruey Tsai)
, 2011-11, (已刊登)

tencon 2010 卷期:752頁~755頁

Design of Multiple RESURF LDMOS with P-top rings and STI regions in 65nm
CMOS Technology

參與研討會

1. 蔡宗叡 2011-11-21~2011-11-24

IEEE TENCON 2011

2. 蔡宗叡 2012-06-04~2012-06-06

IEEE IS3C 2012